

[TuA1] Phosphides

Session Date	July 14 (Tue.), 2026
Session Time	08:30–10:15
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Dr. Emanuele Pelucchi (Tyndall National Institute, Ireland) Dr. Ameer Abdullah (KAIST, Korea)

[TuA1–1] [Invited]

08:30–09:00

Growth Management of InP-Based Optoelectronic and Microelectronic Devices on InP-on-Silicon (InPoSi) Wafers

C. Besancon¹, D. Néel¹, N. Vaissière¹, E. Izquierdo¹, A. Elias¹, G. Daccord¹, J.L. Reverchon¹, O. Delorme¹, A. Wilk¹, N. Davy¹, V. Nodjiadjim¹, C. Mismar¹, F. Fortunato², J. Bergsten³, H. Rodilla², B. Ghyselen⁴, L. Sanchez⁵, T. Bria⁵, F. Fournel⁵, and J. Decobert¹, ¹III–V Lab, France, ²Chalmers University of Technology, Sweden, ³Low Noise Factory, Sweden, ⁴SOITEC, France, ⁵CEA-Leti, France

[TuA1–2]

09:00–09:15

Impact of Growth Parameters on High Quality InP Microridges Grown Directly on On-Axis Si Substrates

T. Meyer¹, A. Baechele¹, M. Prescher¹, L. Kirste¹, R. Keil¹, M. Haertelt¹, P. Merkert¹, S. Messaoudène², L. Andreutti², M. Doron², B. Ben Bakir², A. Trampert³, and R. Aidam¹, ¹Fraunhofer Institute for Applied Solid State Physics IAF, Germany, ²CEA-Leti, France, ³Paul-Drude-Institut für Festkörperelektronik, Germany

[TuA1–3]

09:15–09:30

Orientation Patterned Gallium Phosphide for Integrated Nonlinear Photonics

B. Le Corre^{1,2}, S. Combré³, M. Millotte¹, G. Beaudoin¹, A. Harouri¹, L. Le Gratiet¹, I. Sagnes¹, B. Gérard⁴, A. De Rossi³, A. Grisard³, G. Patriarche¹, Y. Léger², and K. Pantzas¹, ¹Université Paris-Saclay, France, ²Université de Rennes, France, ³Thales Research and Technology, France, ⁴III–V Lab, France

[TuA1-4]

09:30-09:45

WITHDRAWN

[TuA1-5]

09:45-10:00

Resistive Ru-Doped InP Layers for Improved Semi-Insulating Buried Heterostructures

Gustavo Afonso, Nicolas Vaissiere, Antoine Elias, Cosimo Calo, Vladyslav Vakarin, Giancarlo Cerulo, Mokhtar Korti, Olivier Parillaud, Frederic Pommereau, and Jean Decobert, III-V Lab, France

[TuA1-6]

10:00-10:15

In-Situ Reflectometry and Curvature Monitoring for Process Control of InP-Based Laser Heterostructures Grown by MOVPE

K. Haberland¹, J. Decobert², N. Vaissiere², V. Bot², C. Besancon², and F. Weigert¹, ¹LayTec AG, Germany, ²III-V Lab, France